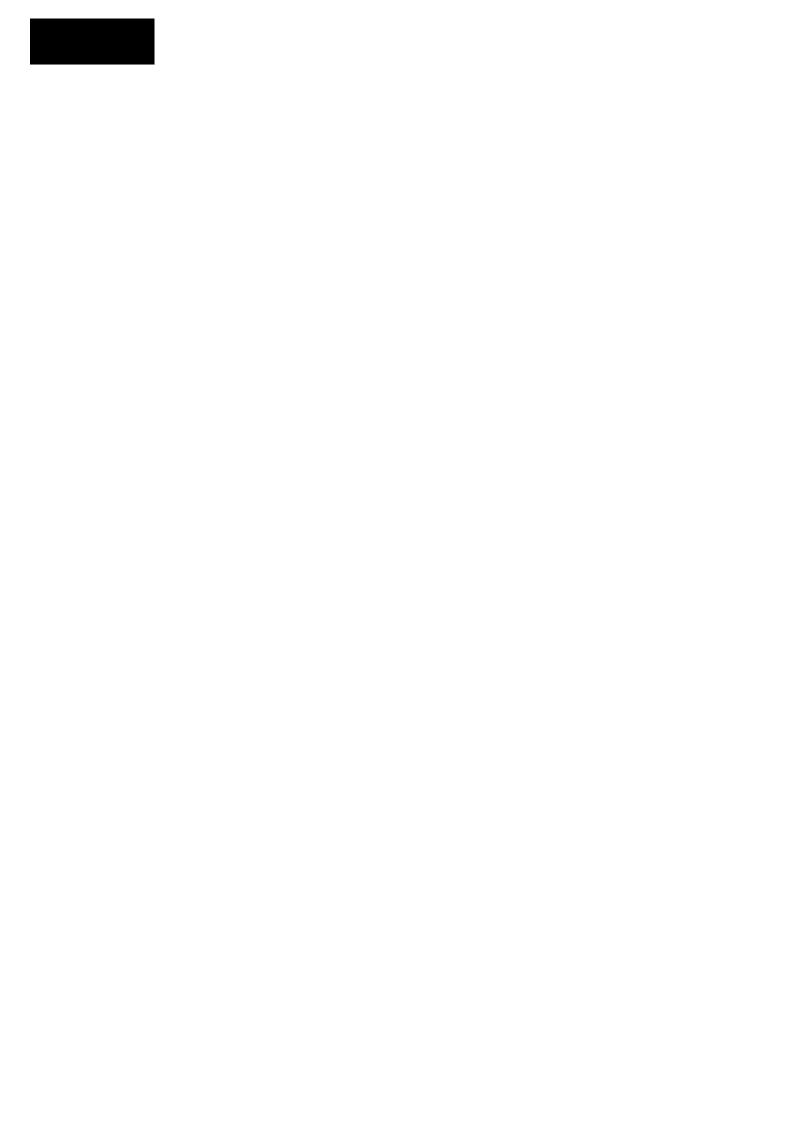
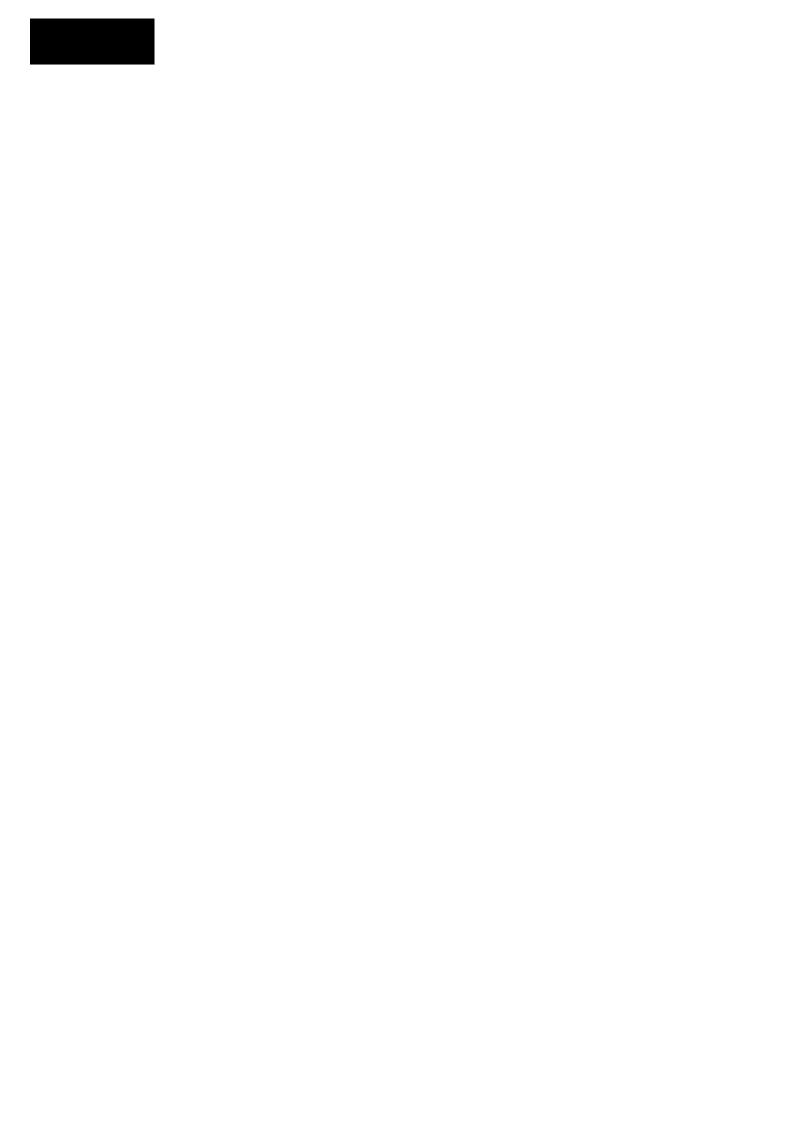
1. FEATURES



LBC847BDW1T1G, S-LBC847BDW1T1G NPN Dual General Purpose Transistors **6.ELECTRICAL CHARACTERISTICS CURVES**



LBC847BDW1T1G, S-LBC847BDW1T1G

NPN Dual General Purpose Transistors

7.OUTLINE AND DIMENSIONS

Notes:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

A2							
	0.15						
	1.80						
		2.10	2.20	0.078	0.082	0.086	
						0.053	
	0.65 BSC			0.026 BSC			
						0.018	
L2	0.15 BSC			0.006 BSC			
	0.15			0.01			
bbb	0.30			0.01			
ccc	0.10			0.00			
ddd		0.10			0.00		

8.SOLDERING FOOTPRINT